

TOSHIBA Transistor Silicon-Germanium NPN Epitaxial Planer Type

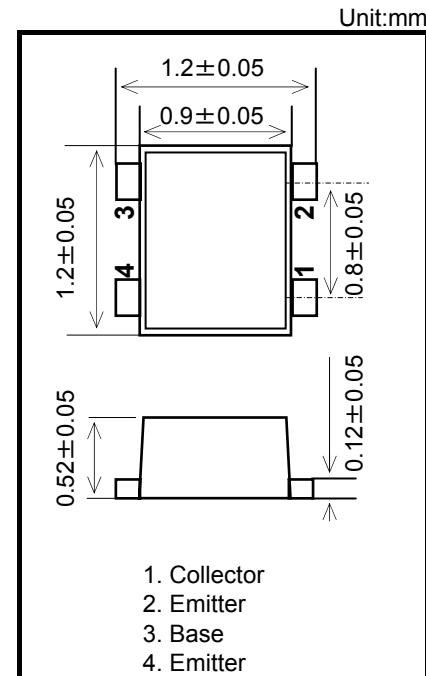
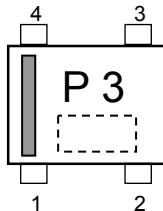
MT4S300T

UHF-SHF Low Noise Amplifier Application

FEATURES

- Low Noise Figure : $NF=0.55\text{dB}(\text{Typ.})$ (@ $f=2\text{GHz}$)
- High Gain : $|S_{21e}|^2=18\text{dB}(\text{Typ.})$ (@ $f=2\text{GHz}$)
- 2 kV ESD robustness (HBM) due to integrated protection circuits

Marking



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Rating	Unit
Collector-Base voltage	V_{CBO}	6	V
Collector-Emitter voltage	V_{CEO}	4	V
Collector-Current	I_C	50	mA
Base-Current	I_B	10	mA
Collector Power dissipation	P_C	100	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature Range	T_{stg}	-55~150	$^\circ\text{C}$

JEDEC	-
JEITA	-
TOSHIBA	2-1G1B

Weight: 1.5mg (Typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Microwave Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Transition Frequency	f_T	$V_{CE}=3V, I_C=20mA$	22.5	26.5	—	GHz
Insertion Gain	$ S_{21e} ^2$	$V_{CE}=3V, I_C=20mA, f=2GHz$	15.5	18	—	dB
Noise Figure	NF	$V_{CE}=3V, I_C=10mA, f=2GHz$	—	0.55	0.7	dB

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector Cut-off Current	I_{CBO}	$V_{CB}=5V, I_E=0$	—	—	0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=3V, I_C=10mA$	200	—	400	-
Reverse Transfer Capacitance	C_{re}	$V_{CB}=1V, I_E=0, f=1MHz$ (Note 1)	—	0.16	0.27	pF

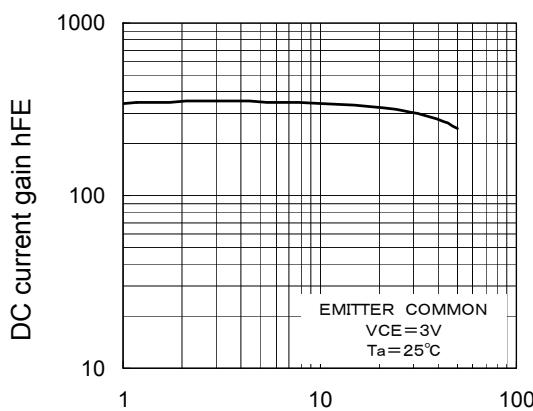
Note 1: C_{re} is measured by 3 terminal method with capacitance bridge.

Caution:

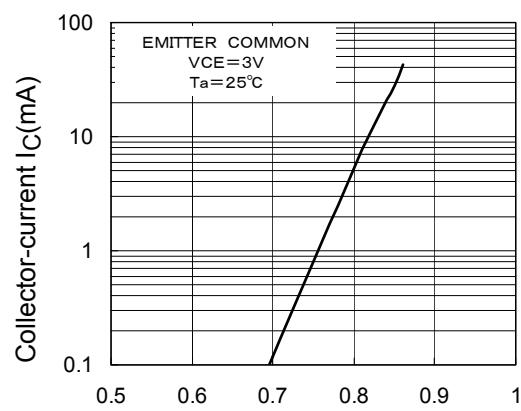
This device is due to applied the high frequency transistor process of $f_T=100GHz$ class is used for this product.

Please make enough tool and equipment earthed when you handle.

h_{FE} - I_C



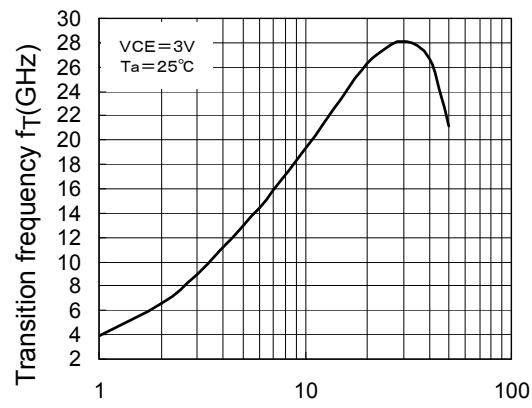
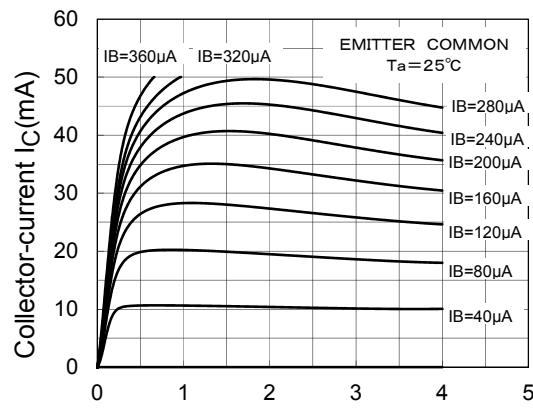
I_C - V_{BE}



Collector-current I_C (mA)

Base-emitter voltage V_{BE} (V)

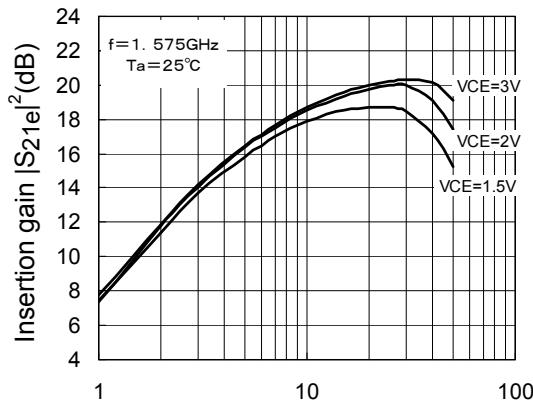
I_C - V_{CE}



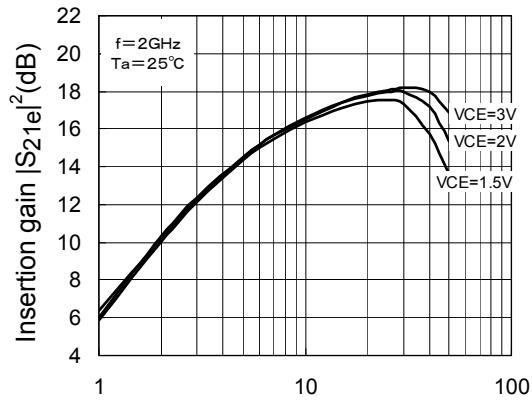
Collector-emitter voltage V_{CE} (V)

Collector-current I_C (mA)

$|S_{21e}|^2$ - I_C

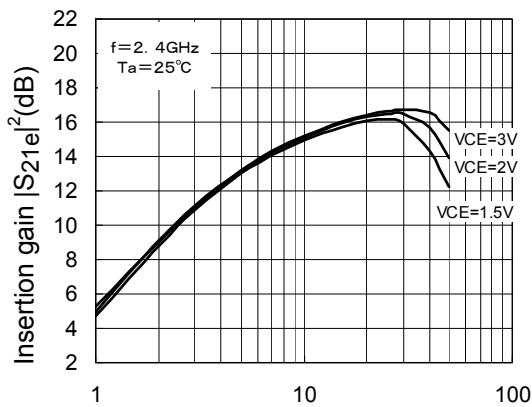


Collector-current I_C (mA)

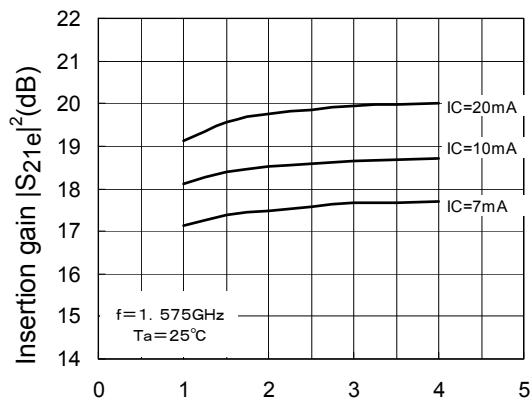


Collector-current I_C (mA)

$|S_{21e}|^2 - I_C$



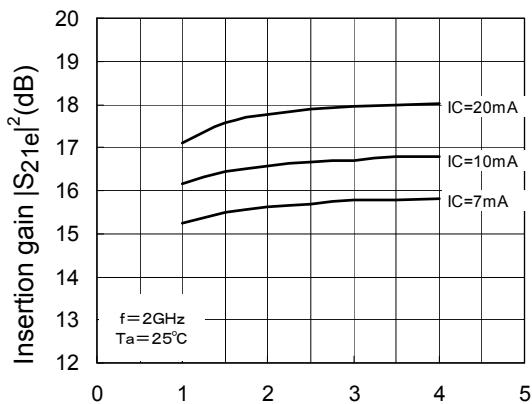
$|S_{21e}|^2 - V_{CE}$



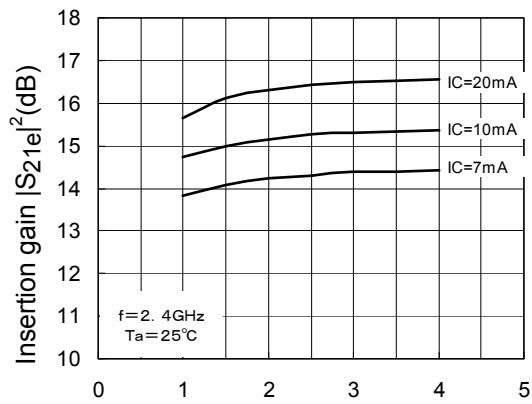
Collector-current I_C (mA)

Collector-emitter voltage V_{CE} (V)

$|S_{21e}|^2 - V_{CE}$



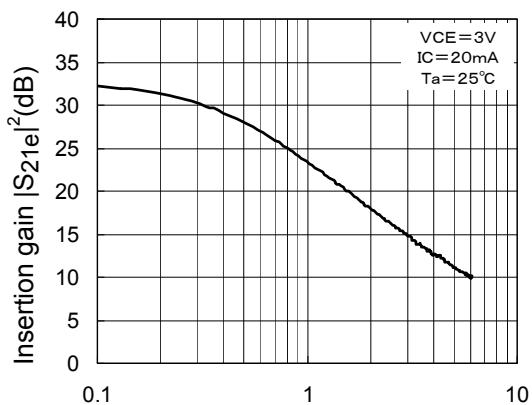
$|S_{21e}|^2 - V_{CE}$



Collector-emitter voltage V_{CE} (V)

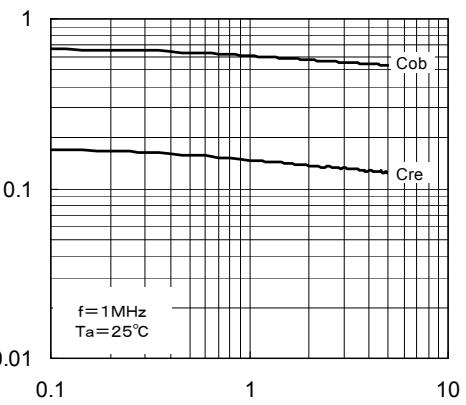
Collector-emitter voltage V_{CE} (V)

$|S_{21e}|^2 - \text{Freq.}$

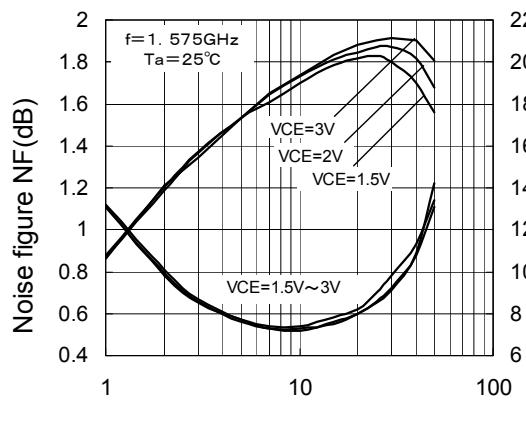
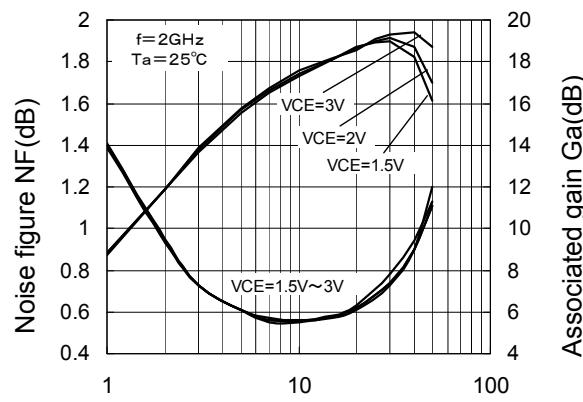
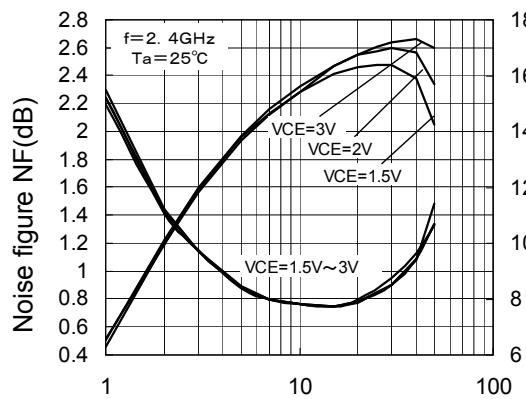
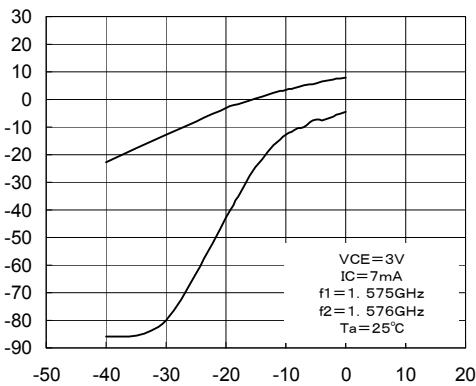
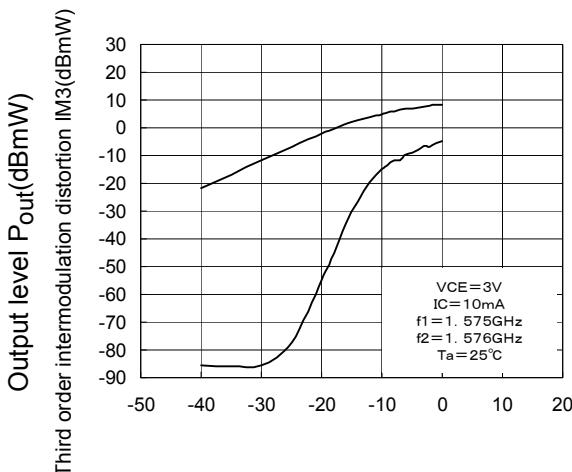
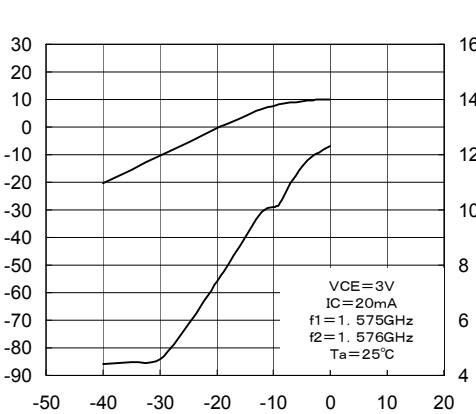


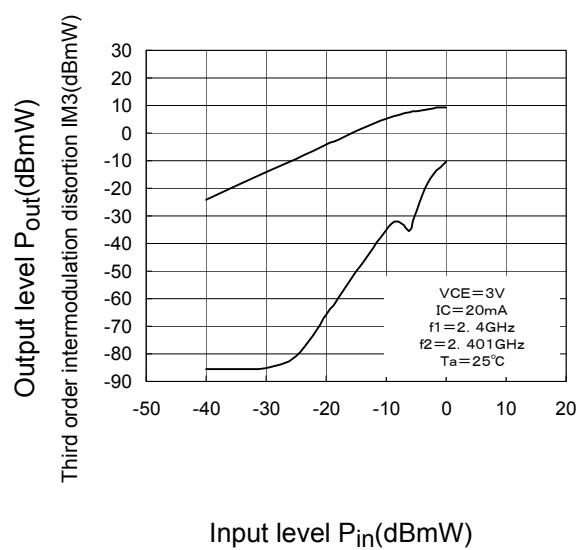
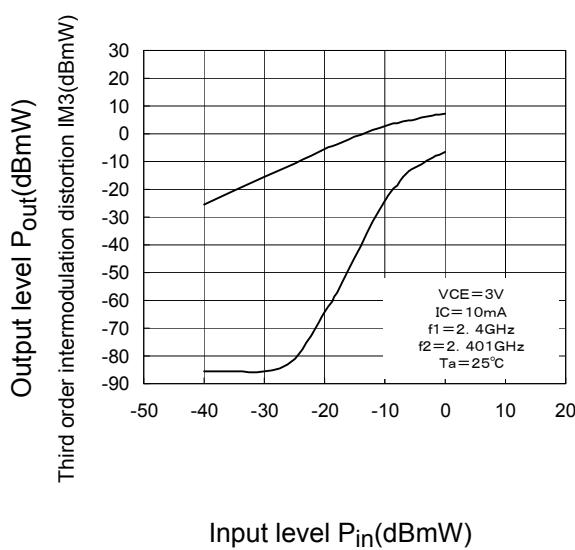
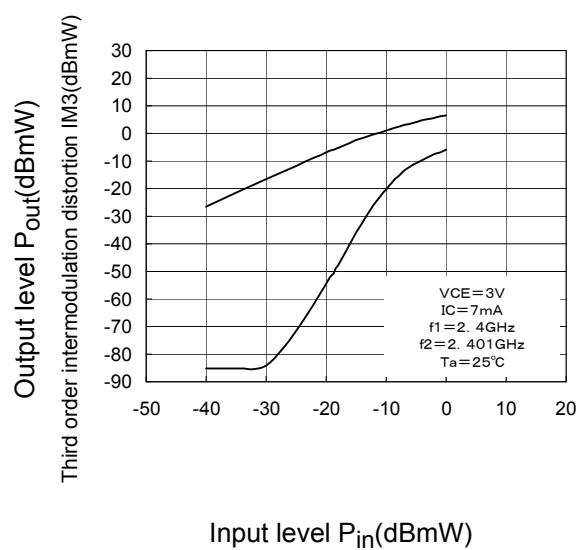
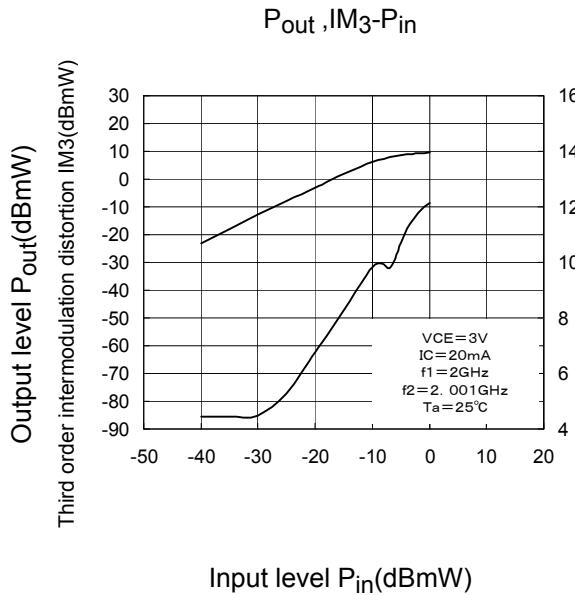
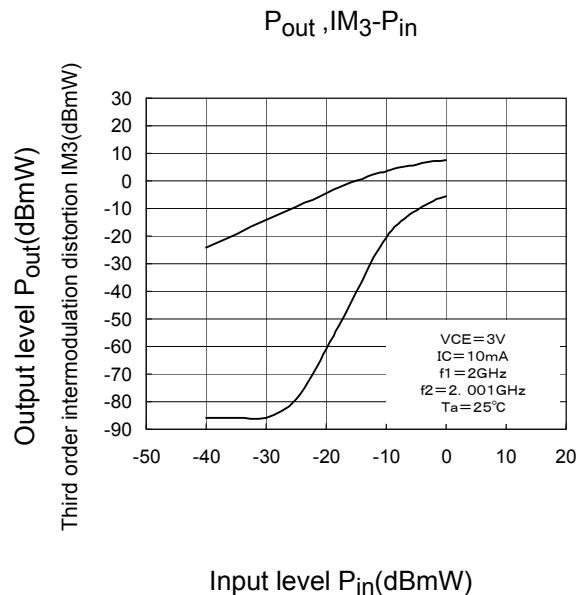
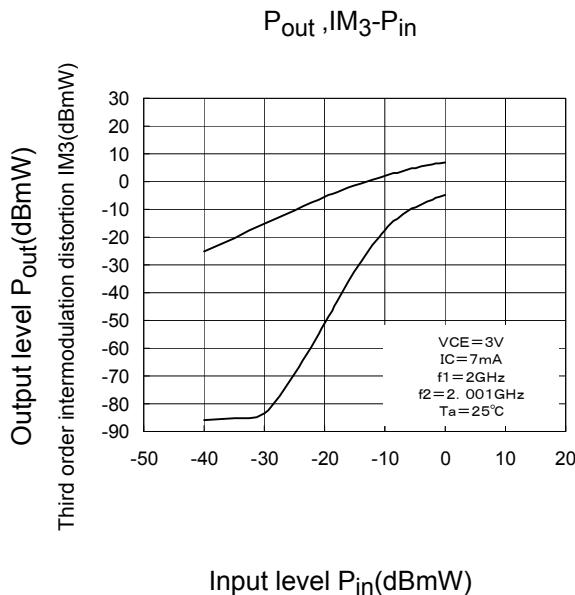
Frequency f (GHz)

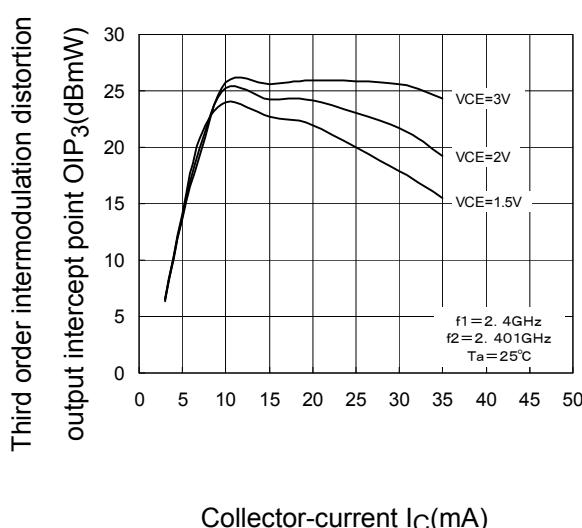
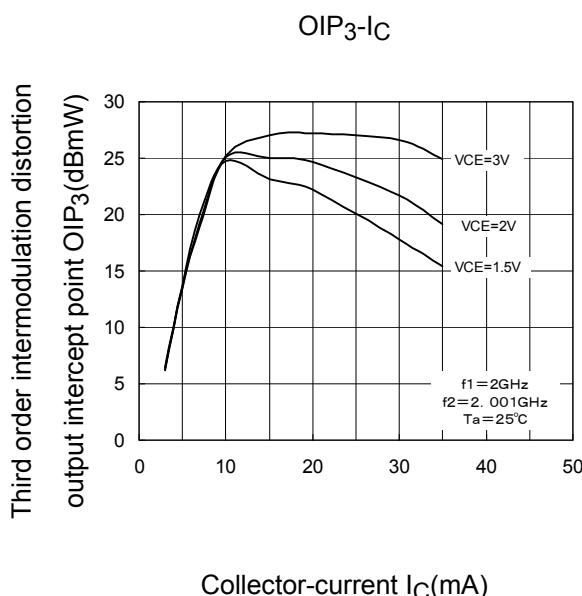
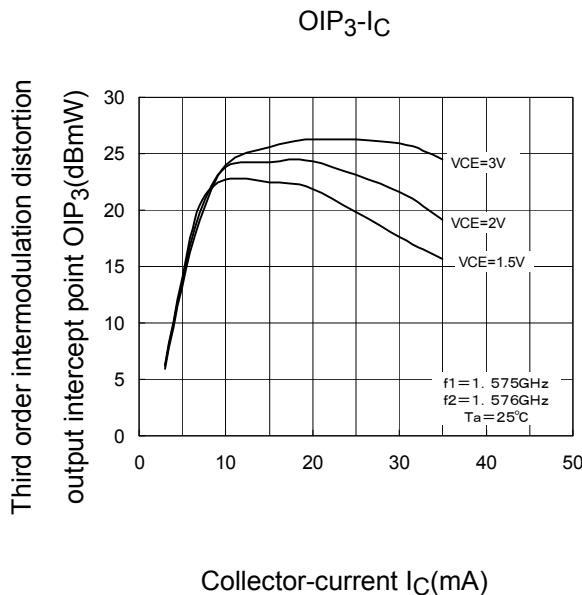
Reverse transfer capacitance C_{re} (pF)
Output capacitance C_{ob} (pF)



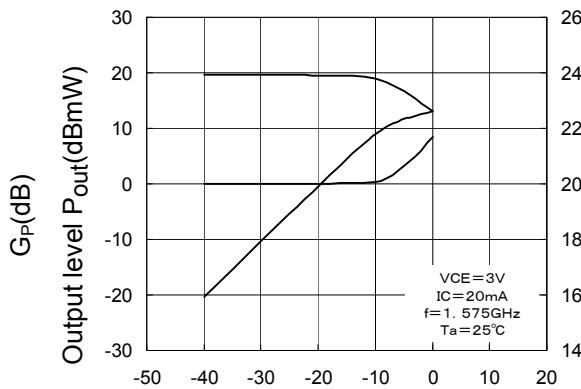
Collector-base voltage V_{CB} (V)

NF ,Ga- I_C NF ,Ga- I_C Collector-current I_C (mA)Collector-current I_C (mA)NF ,Ga- I_C Associated gain G_a (dB)
Output level P_{out} (dBmW)
Third order intermodulation distortion $IM3$ (dBmW)P_{out},IM₃-P_{in}Collector-current I_C (mA)Input level P_{in} (dBmW)P_{out},IM₃-P_{in}Output level P_{out} (dBmW)
Third order intermodulation distortion $IM3$ (dBmW)P_{out},IM₃-P_{in}Input level P_{in} (dBmW)Input level P_{in} (dBmW)

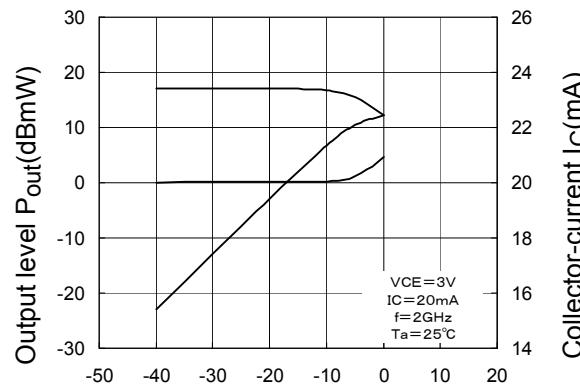




$P_{out}, G_P, I_C - P_{in}$



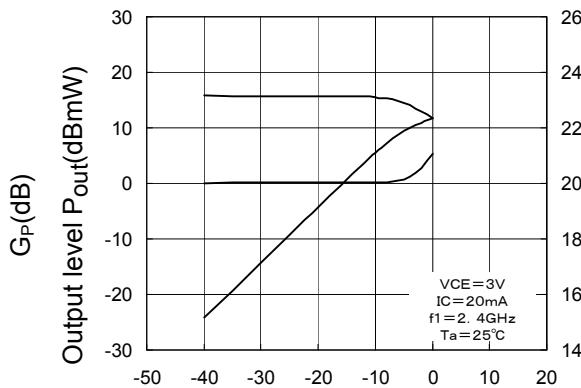
$P_{out}, G_P, I_C - P_{in}$



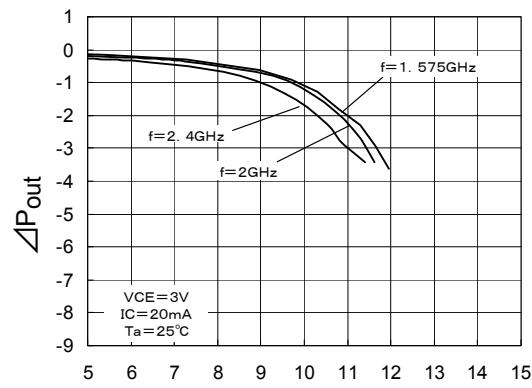
Input level P_{in} (dBmW)

Input level P_{in} (dBmW)

$P_{out}, G_P, I_C - P_{in}$



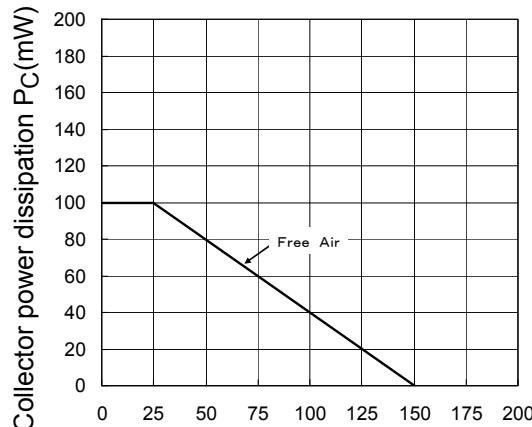
$\Delta P_{out} - P_{out}$



Input level P_{in} (dBmW)

Output level P_{out} (dBmW)

$P_C - T_a$



Ambient temperature T_a (°C)

Note2: The graphs indicate nominal characteristics.

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